

描述 / Descriptions

SOT-23 塑封封装 P 道场效应管。

P- CHANNEL MOSFET in a SOT-23 Plastic Package.

特征 / Features

$V_{DS} = -30V$ $I_D = -3.2A$

$R_{DS(ON)} @ -10V \leq 90m\Omega$ (Typ. 54m Ω)

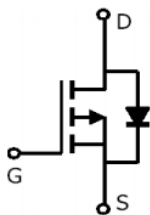
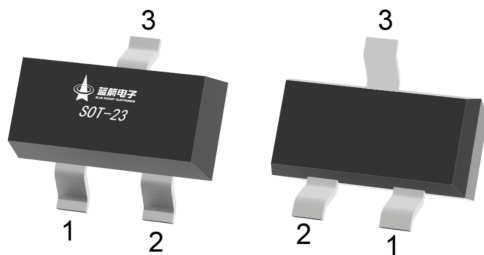
$R_{DS(ON)} @ -4.5V \leq 110m\Omega$ (Typ. 63m Ω)

无卤产品。HF Product.

用途 / Applications

笔记本，负载开关，电池保护，手持仪器。

Notebook, Load Switch, Battery Protection, Hand-held Instruments.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

PIN 1 : G

PIN 2 : S

PIN 3 : D

印章代码 / Marking

见印章说明。

See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter		符号 Symbol	数值 Rating	单位 Unit
Drain–Source Voltage		V _{DSS}	-30	V
Gate–Body Leakage Voltage		V _{GSS}	±12	V
Drain Current – Continuous		I _D	-3.2	A
Pulsed Drain Current		I _{DM}	-13.2	A
Power Dissipation		P _D	1.5	W
Operating and Storage Temperature Range		T _J , T _{STG}	-55~150	°C
Maximum Junction-to-Ambient	t ≤ 10s	R _{θJA}	83.3	°C/W
Maximum Junction-to-Ambient	Steady-State		125	°C/W
Maximum Junction-to-Lead	Steady-State	R _{θJL}	80	°C/W

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V I _D =-250μA	-30	-33		V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =-250μA	-0.5		-1.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V I _D =-3A		54	90	mΩ
		V _{GS} =-4.5V I _D =-2A		63	110	mΩ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V V _{GS} =0V			-1.0	μA
Gate-Body leakage current	I _{GSS}	V _{GS} =±12V V _{DS} =0V			±100	nA
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V I _S =-1A T _J =25°C			-1.2	V
Gate resistance	R _g	f=1MHz		7.5		Ω
Input Capacitance	C _{iss}	V _{DS} =-15V V _{GS} =0V f=1.0MHz		350		pF
Output Capacitance	C _{oss}			45		
Reverse Transfer Capacitance	C _{rss}			25		
Total Gate Charge	Q _g (10V)	V _{DS} =-15V V _{GS} =-10V I _D =-3A		5.2		nC
Total Gate Charge	Q _g (4.5V)			2.7		
Gate-to-Source Charge	Q _{gs}			1.1		
Gate-to-Drain Charge	Q _{gd}			1.3		
Turn-On Delay Time	t _{d(on)}	V _{DS} =-15V V _{GS} =-10V R _L =5Ω R _{GEN} =3Ω		8.5		ns
Turn-On Rise Time	t _r			4		
Turn-Off Delay Time	t _{d(off)}			13.2		
Turn-Off Fall Time	t _f			4.3		

电参数曲线图 / Electrical Characteristic Curve

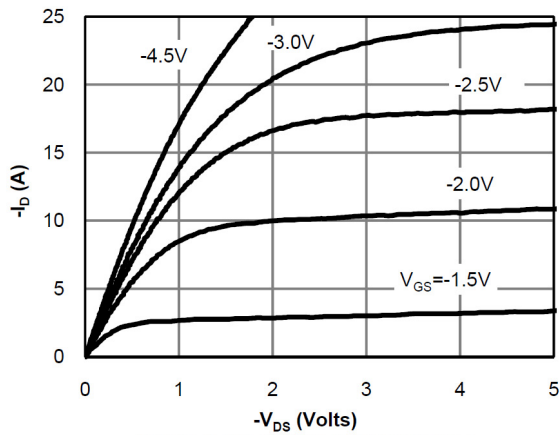


Figure 1: On-Region Characteristics

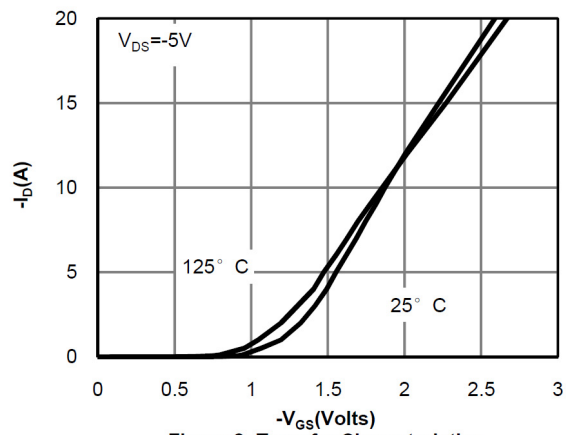


Figure 2: Transfer Characteristics

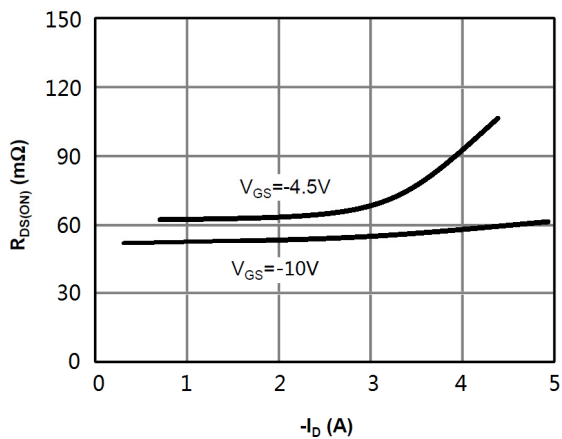


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

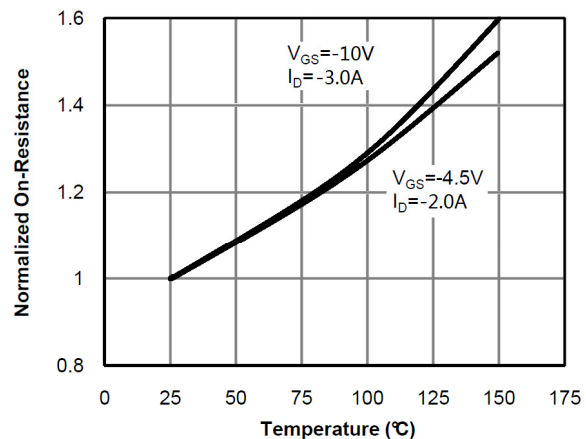


Figure 4: On-Resistance vs. Junction Temperature

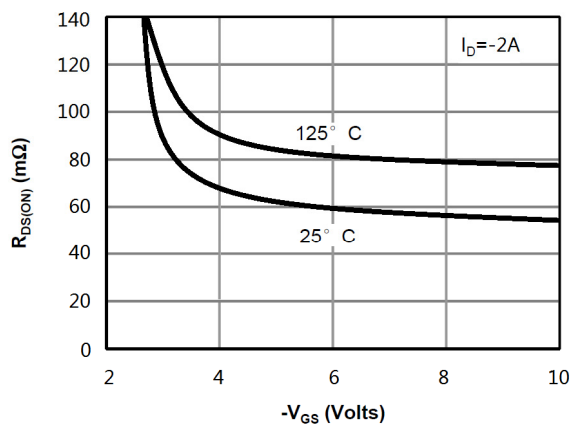


Figure 5: On-Resistance vs. Gate-Source Voltage

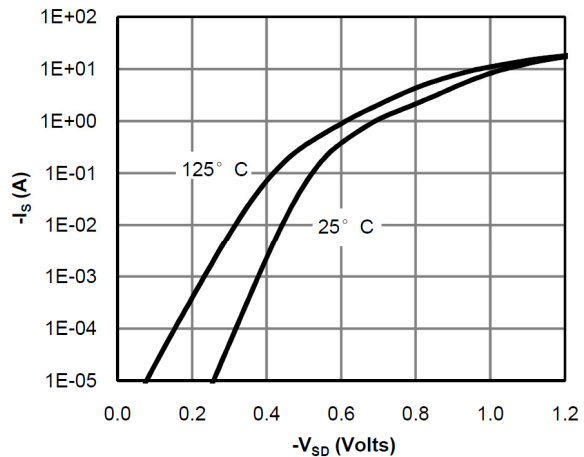
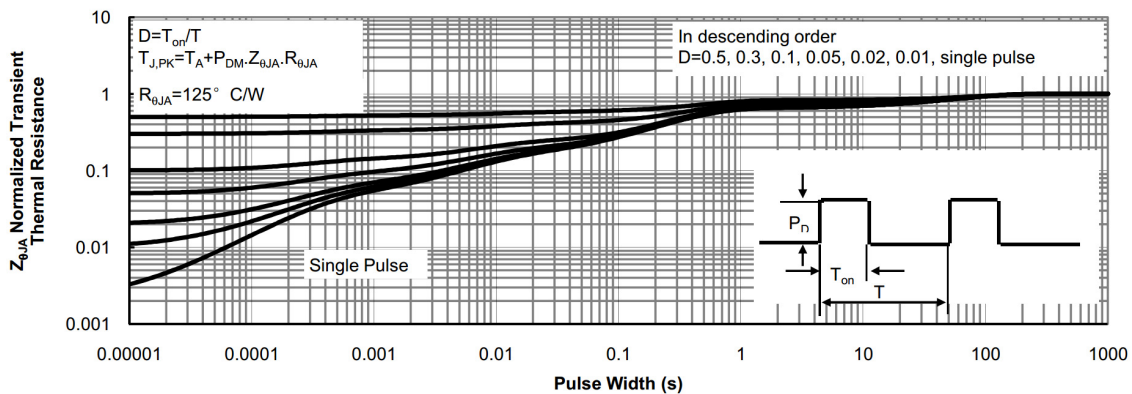
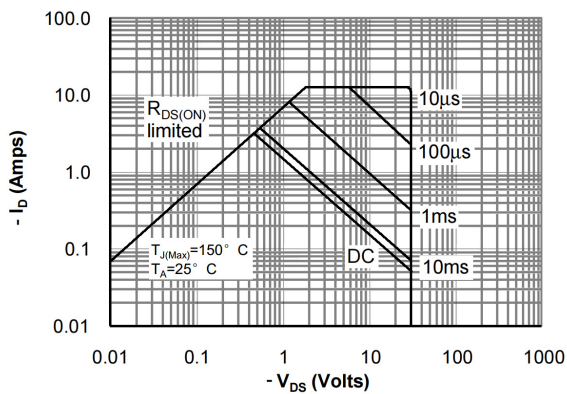
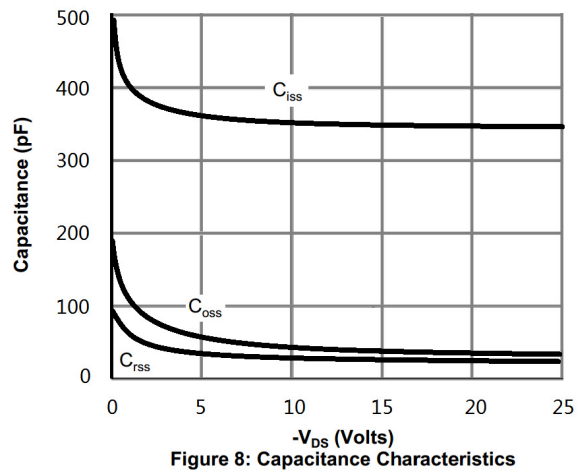
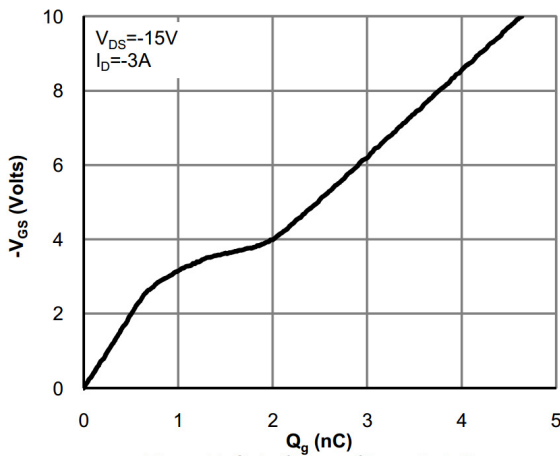


Figure 6: Body-Diode Characteristics

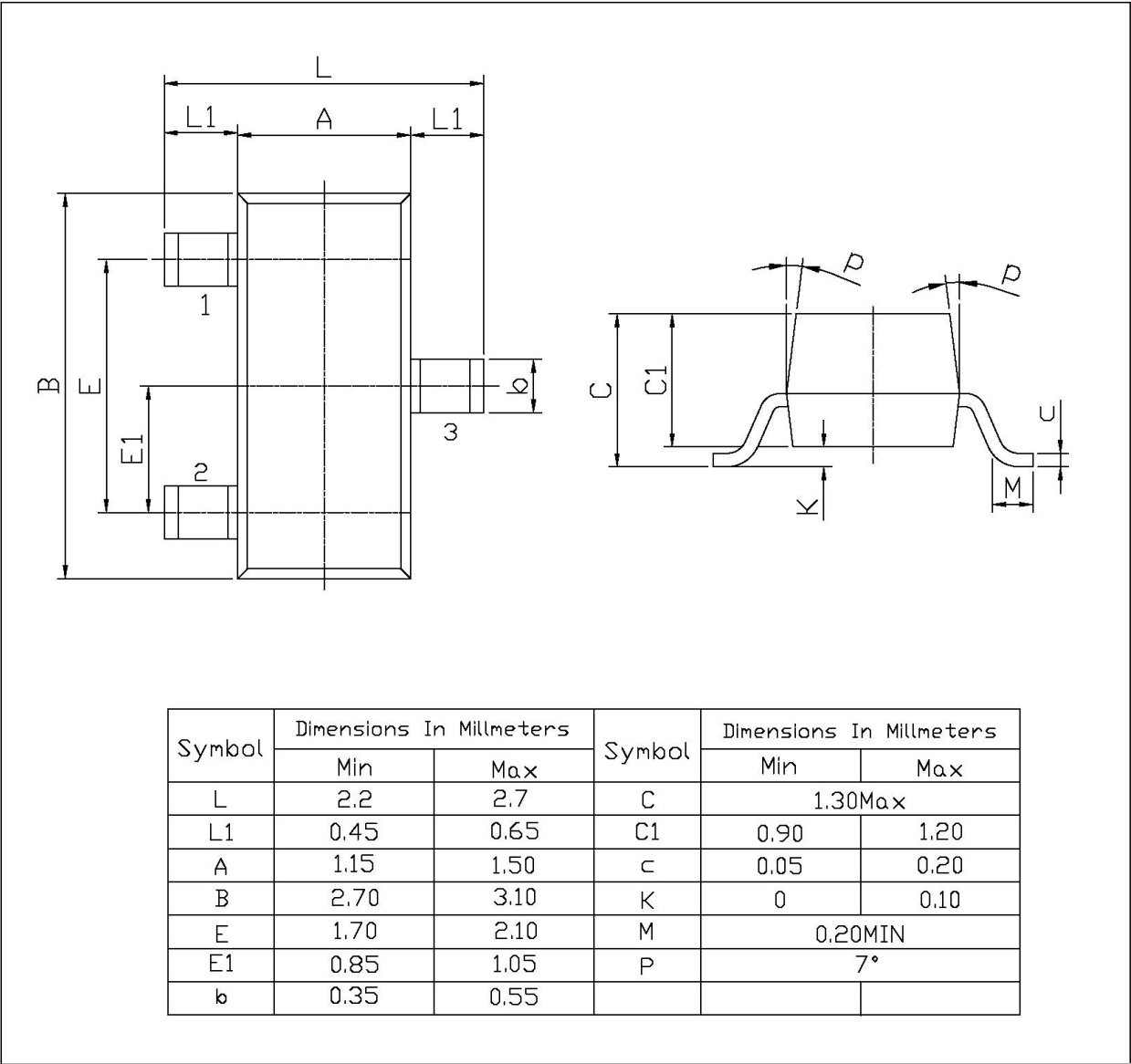
电参数曲线图 / Electrical Characteristic Curve



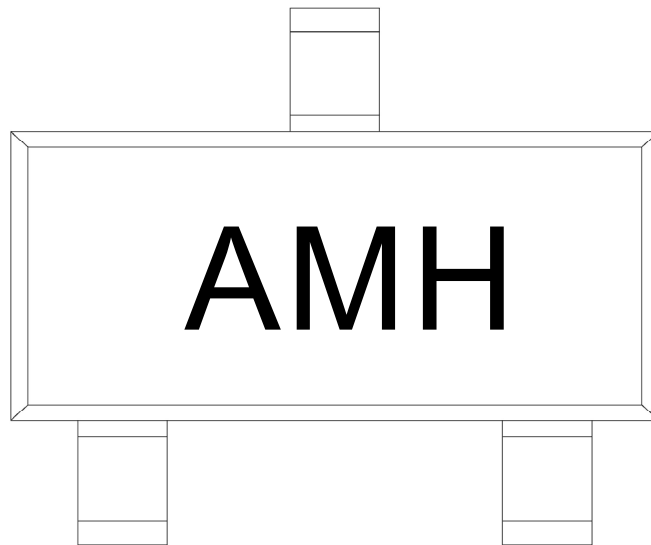
外形尺寸图 / Package Dimensions

SOT-23

单位：mm



印章说明 / Marking Instructions



说明：

H: 为公司代码

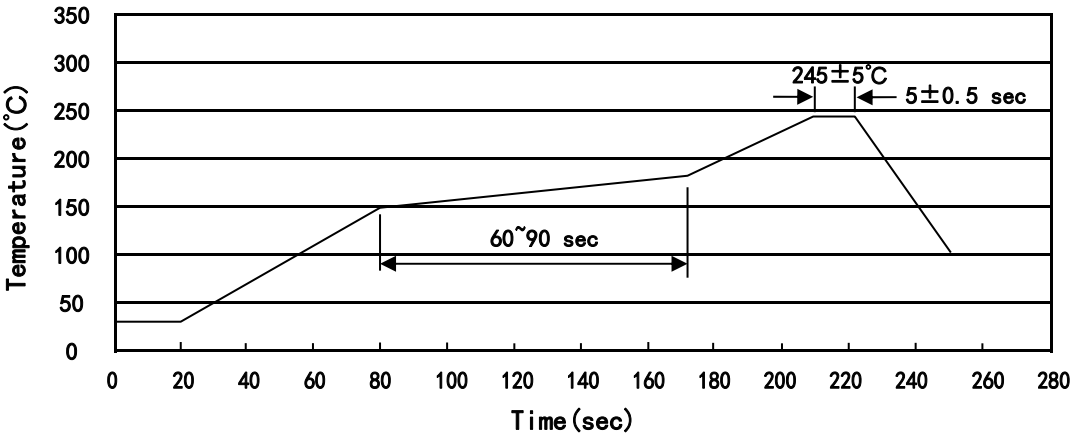
AM: 为型号代码

Note:

H: Company Code

AM: Product Type

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C 时间：10±1 sec. Temp.:260±5°C Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	6	180,000	7" ×8	180×120×180	390×385×205

使用说明 / Notices